

**Low Capacitance ESD/Surge Protection
for Gigabit Ethernet Interfaces**

◆ **DESCRIPTIONS**

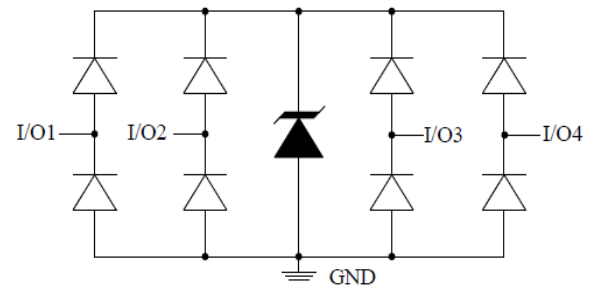
CMESDF10V2R5C3R8DFE is a low-capacitance Transient Voltage Suppressor (TVS) array designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 3.8pF only, CMESDF10V2R5C3R8DFE is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ($\pm 15\text{kV}$ air, $\pm 8\text{kV}$ contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), IEC 61000-4-5 (Surge) (25A, 8/20 μs), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

CMESDF10V2R5C3R8DFE is in a DFN2.6 \times 2.6-10L package. Each CMESDF10V2R5C3R8DFE device can protect two high-speed line pairs. The combined features of low capacitance and high ESD robustness make CMESDF10V2R5C3R8DFE ideal for high-speed data port and high-frequency line (e.g., Gigabit Ethernet Ports) applications. The low clamping voltage of the CMESDF10V2R5C3R8DFE guarantees a minimum stress on the protected IC.

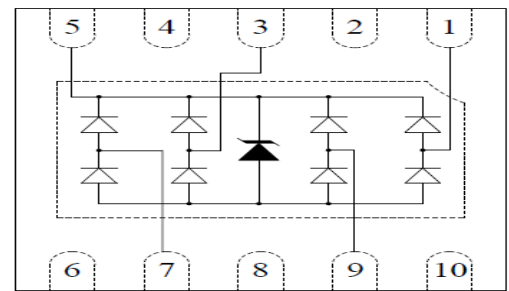
◆ **FEATURES**

- 1、Transient protection for high-speed data lines
IEC 61000-4-2 (ESD) $\pm 15\text{kV}$ (Air)
 $\pm 8\text{kV}$ (Contact)
IEC 61000-4-4 (EFT) 40A (5/50 ns)
IEC 61000-4-5 (Surge) 25A (8/20 μs)
- 2、Package optimized for high-speed lines
- 3、Provides protection for two line pairs
- 4、Low capacitance: 3.8pF @ 0V (Typical)
- 5、Low leakage current: 0.1 μA @ V_{RWM} (Typical)
- 6、Low operating and clamping voltage
- 7、Each I/O pin can withstand over 1000 ESD strikes for $\pm 8\text{kV}$ contact discharge

◆ **Circuit Diagram**



◆ **Pin Configuration**



DFN2.6 \times 2.6-10L (Top View)

◆ **Applications**

- 1、10/100/1000M Ethernet Ports
- 2、WAN/LAN Equipment
- 3、Desktops, Servers and Notebooks
- 4、Cellular Phones
- 5、Switching Systems
- 6、Audio/Video Inputs

◆ **Mechanical Characteristics**

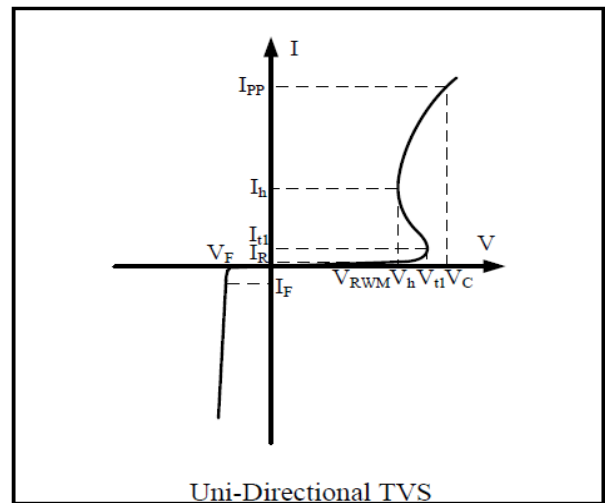
- 1、DFN2.6 \times 2.6-10L package
- 2、Flammability Rating: UL 94V-0
- 3、Marking: Part number, Date
- 4、Packaging: Tape and Reel

◆ **Absolute Maximum Rating**

Symbol	Parameter	Value	Units
I_{PP}	Peak Pulse Current (8/20 μ s)	25	A
P_{PK}	Peak Pulse Power (8/20 μ s)	450	W
V_{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	± 25 ± 15	kV
T_{OPT}	Operating Temperature	-55/+125	$^{\circ}$ C
T_{STG}	Storage Temperature	-55/+150	$^{\circ}$ C

◆ **Electrical Characteristics (T = 25 $^{\circ}$ C)**

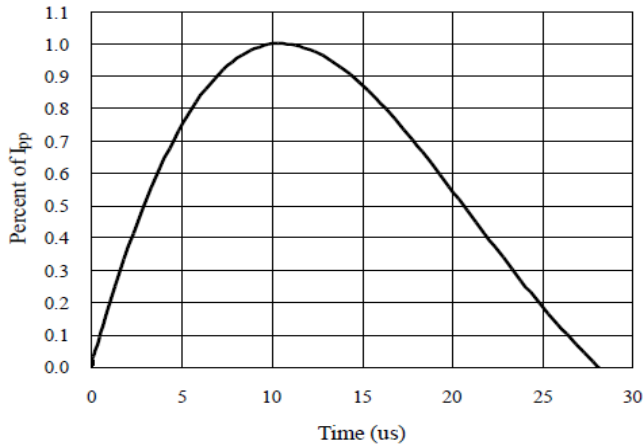
Symbol	Parameter
I_R	Reverse Leakage Current @ V_{RWM}
V_{t1}	Trigger Voltage
I_{t1}	Trigger Current @ V_{t1}
V_h	Holding Voltage
I_h	Holding Current @ V_h
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Maximum Peak Pulse Current
V_F	Forward Voltage @ I_F
C_{ESD}	Parasitic Capacitance



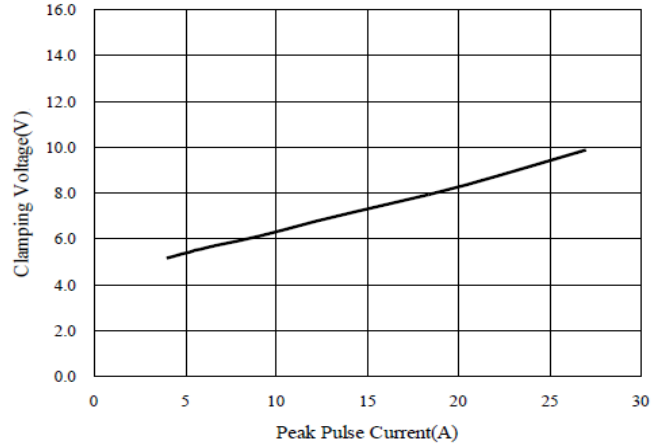
Symbol	Test Condition	Minimum	Typical	Maximum	Units
V_{RWM}		-	-	2.5	V
I_R	$V_{RWM} = 2.5V, T = 25^{\circ}C$		0.1	1.0	μ A
V_{t1}	$I_{t1} = 1\mu A$	3.0	3.7	4.5	V
V_h	$I_h = 1mA$	3.0		4.0	V
V_C	$I_{PP} = 1A, tp = 8/20\mu s$ (Each Line)	-	-	4.5	V
V_C	$I_{PP} = 10A, tp = 8/20\mu s$ (Each Line)	-	-	7.5	V
V_C	$I_{PP} = 25A, tp = 8/20\mu s$ (Each Line)	-	-	15.0	V
C_{ESD}	Between I/O Pins and Ground $V_R = 0V, f = 1MHz$	-	3.8	5.0	pF
C_{ESD}	Between I/O Pins $V_R = 0V, f = 1MHz$	-	2.0	2.5	pF

◆ TYPICAL ELECTRICAL CHARACTERISTICS CURVE

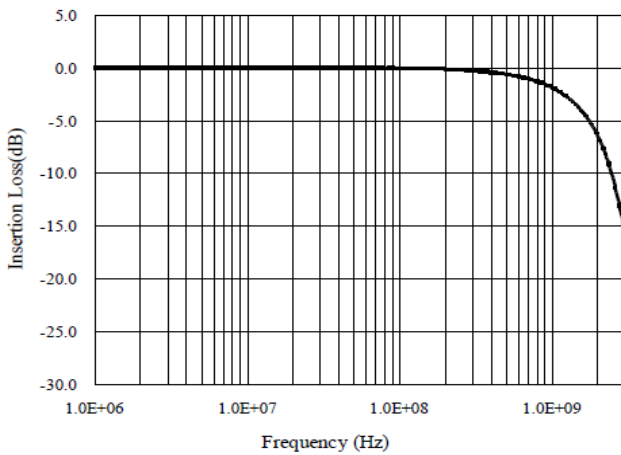
8/20 μ s Pulse Waveform



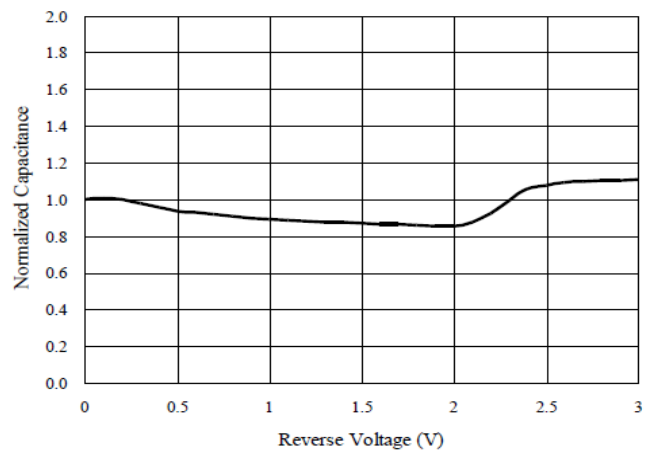
Clamping Voltage V_C vs. Current I_{PP}



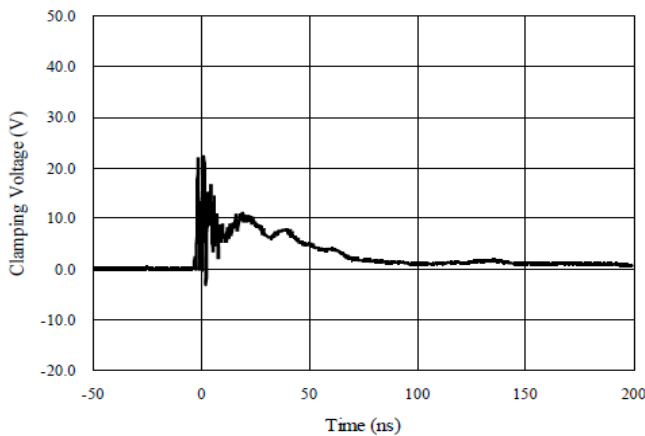
Insertion Loss S21



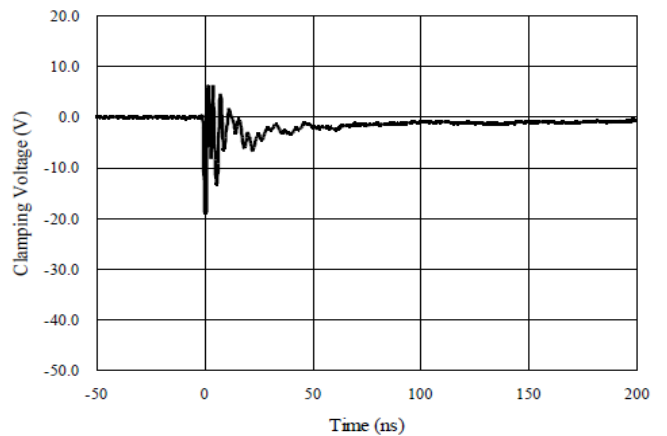
Normalized Capacitance vs. Voltage



ESD Clamping of I/O to GND
(+8kV Contact per IEC 61000-4-2)



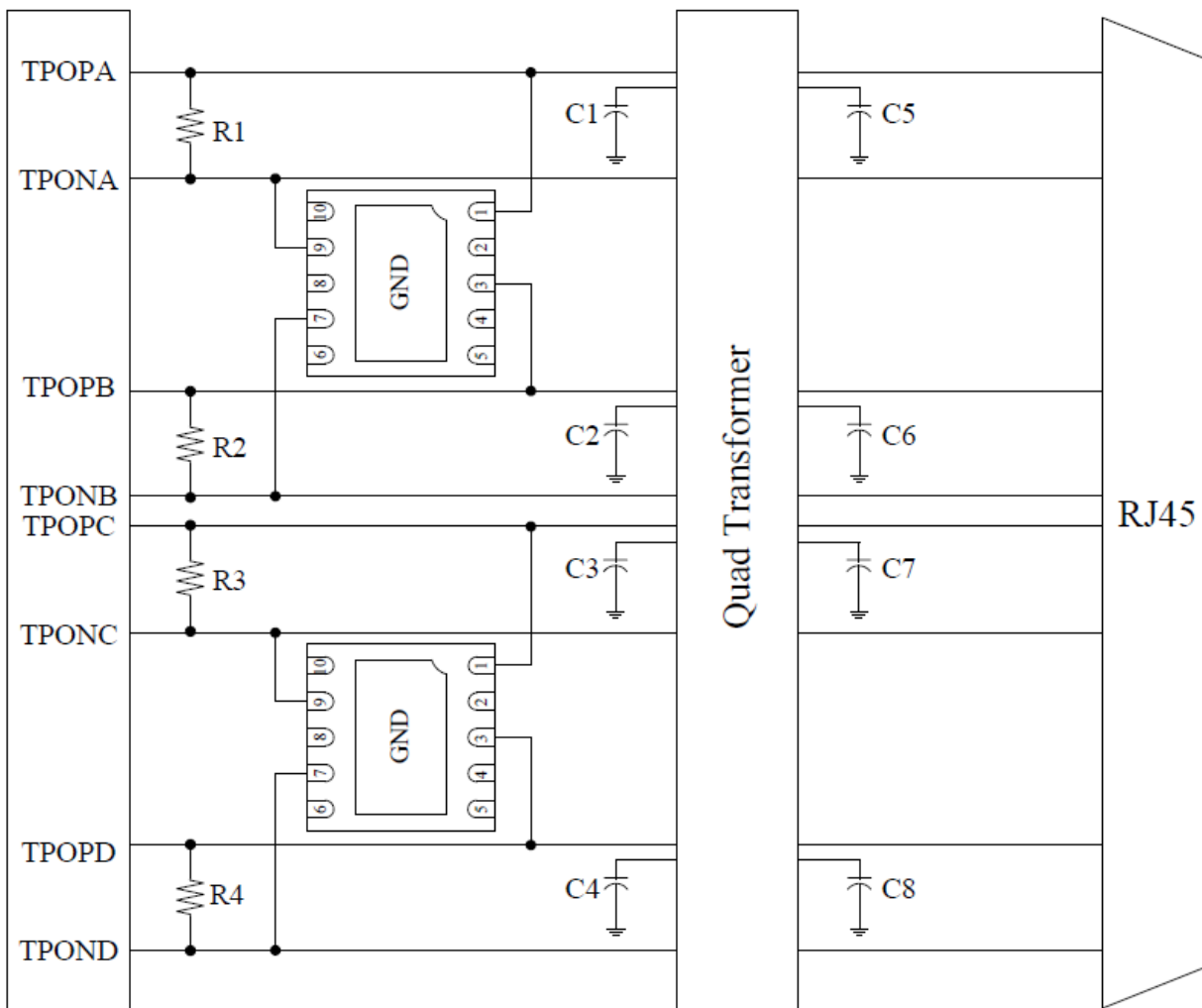
ESD Clamping of I/O to GND
(-8kV Contact per IEC 61000-4-2)



◆ **Application Information**

Electronic equipment is susceptible to damage caused by a variety of sources, including Electrostatic Discharge (ESD), Electrical Fast Transients (EFT) and Lightning strikes. The CMESDF10V2R5C3R8DFE was designed to protect the sensitive equipment from damage which may be induced by such transient events. This product can be configured in different connections to meet the requirement of common-mode and differential-mode as follows:

◆ **Gigabit Ethernet Protection**

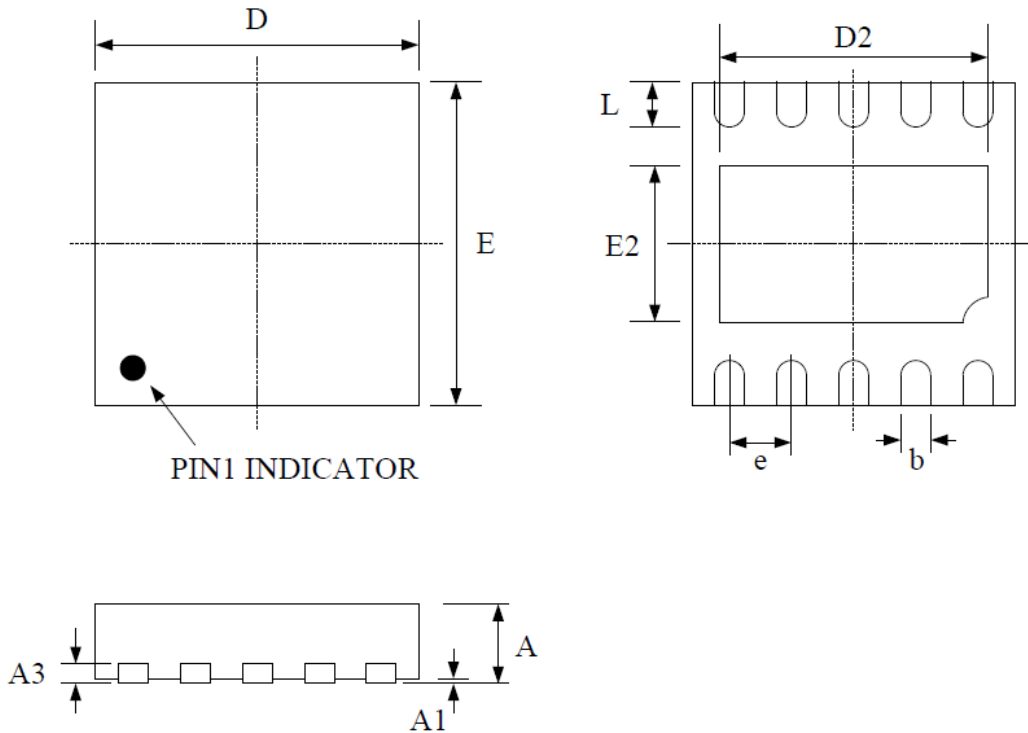


Schematic Diagram for Gigabit Ethernet ESD/Surge Protection using CMESDF10V2R5C3R8DFE

NOTE:

DO NOT connect pin5 of CMESDF10V2R5C3R8DFE to a DC supply.

◆ PACKAGE OUTLINE



Package Dimensions (Controlling dimensions are in millimeters)

Symbol	Dimensions (mm)			Dimensions (Inches)		
	Minimum	Typical	Maximum	Minimum	Typical	Maximum
A	0.500	0.550	0.600	0.020	0.022	0.024
A1	0.000	—	0.050	0.000	—	0.002
A3	0.15 REF			0.006 REF		
b	0.200	0.250	0.300	0.008	0.010	0.012
D	2.550	2.600	2.650	0.100	0.102	0.104
D2	2.000	2.150	2.250	0.079	0.085	0.089
e	0.500 BSC			0.020 BSC		
E	2.550	2.600	2.650	0.100	0.102	0.104
E2	1.110	1.260	1.360	0.044	0.050	0.054
L	0.250	0.350	0.450	0.010	0.014	0.018